

L Number	Hits	Search Text	DB	Time stamp
1	18474	semiconductor and (SRAM or (static adj random adj access adj memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 10:04
2	1049	(semiconductor and (SRAM or (static adj random adj access adj memory))) and (load adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 10:05
4	9	((semiconductor and (SRAM or (static adj random adj access adj memory))) and (load adj transistor)) and gate and drain and source) and ((cell or mobile) adj phone)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 10:06
3	806	((semiconductor and (SRAM or (static adj random adj access adj memory))) and (load adj transistor)) and gate and drain and source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 10:07

L Number	Hits	Search Text	DB	Time stamp
1	3931	(257/296, "369").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 11:58

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L1: Entry 1 of 1

File: JPAB

Feb 13, 1998

PUB-NO: JP410041409A

DOCUMENT-IDENTIFIER: JP 10041409 A

TITLE: SEMICONDUCTOR DEVICE

PUBN-DATE: February 13, 1998

INVENTOR-INFORMATION:

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APPL-NO: JP08211856

APPL-DATE: July 23, 1996

INT-CL (IPC): H01 L 21/8244; H01 L 27/11; H01 L 27/10; H01 L 27/108; H01 L 21/8242

ABSTRACT:

PROBLEM TO BE SOLVED: To enable the wiring density to be lowered by a memory cell of a SRAM by providing the first and second cells with the wiring formed of the same semiconductor layer following the second layer.

SOLUTION: The wirings 27a, 27b for intersection coupling are formed of polycrystalline Si film 36 in the same layer as the polycrystalline Si layer used for the formation of the electrode, etc., of capacitance element in the memory cell of a DRAM to be the polycrystalline Si film after the second layer on an Si substrate. Next, the polycrystalline Si film 36, etc., are covered with an interlayer insulating film. In the memory cell of SRAM in ASIC, the wirings 27a, 27b for intersection coupling are formed of the polycrystalline Si film 36 in the same layer as that of the polycrystalline Si film for the formation of the electrode, etc., of capacity in the memory cell of a DRAM. Accordingly, in comparison with the memory cell of SRAM in the ASIC forming the wirings 27a, 27b of Al films, the density of the Al film wiring is lower than that of the memory cell so that the wirings 27a, 27b may be hardly affected by pattern deformation, or raising dust in the wiring formation step.

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